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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China











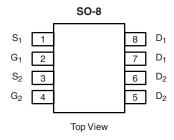
Dual N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
30	0.036 at V _{GS} = 10 V	5.9		
	0.053 at V _{GS} = 4.5 V	4.9		

FEATURES

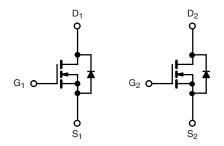
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si4936ADY-T1-E3 (Lead (Pb)-free)

Si4936ADY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	$T_A = 25$ °C, unles	ss otherwise r	noted		_	
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	30			
Gate-Source Voltage		V _{GS}	± 20		V	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I _D	5.9	4.4		
	T _A = 70 °C		4.7	3.6		
Pulsed Drain Current		I _{DM}	± 30		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	1.7	0.9		
	T _A = 25 °C	P _D	2.0 1.1		W	
Maximum Power Dissipation ^a	T _A = 70 °C	L D	1.3	0.7	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Mariana Indiana Indiana	t ≤ 10 s	R _{thJA}	50	62.5	
Maximum Junction-to-Ambient ^a	Steady State	¹ ¹thJA	90	110	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	32	40	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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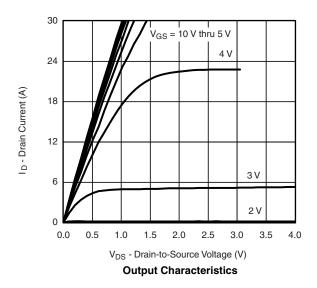
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1.0		3.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zava Cata Valtaga Dvain Current	1	V _{DS} = 30 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α	
		$V_{GS} = 10 \text{ V}, I_D = 5.9 \text{ A}$		0.032	0.036	Ω	
Drain-Source On-State Resistance ^a	^R DS(on)	$R_{DS(on)}$ $V_{GS} = 4.5 \text{ V}, I_D = 4.9 \text{ A}$		0.042	0.053		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 5.9 \text{ A}$		15		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 1.7 A, V _{GS} = 0 V		0.8	1.2	V	
Dynamic ^b							
Total Gate Charge	Qg			13	20		
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 5.9 \text{ A}$		2.3		nC	
Gate-Drain Charge	Q_{gd}			2.0		1	
Turn-On Delay Time	t _{d(on)}			6	12		
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω		14	25		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 10 V, R_G = 6 Ω		30	60	ns	
Fall Time	t _f			5	10	1	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.7 A, dI/dt = 100 A/μs		30	60		

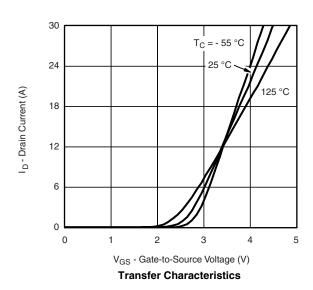
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

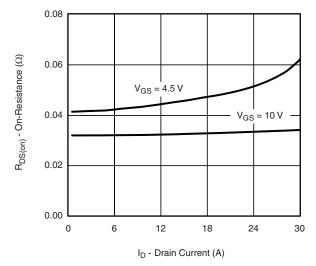




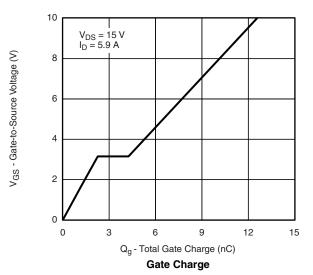


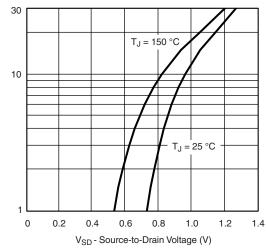


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

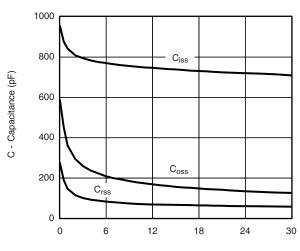


On-Resistance vs. Drain Current



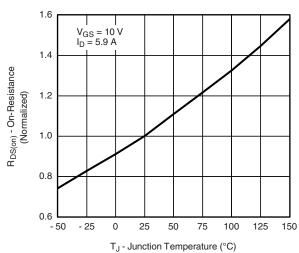


Source-Drain Diode Forward Voltage

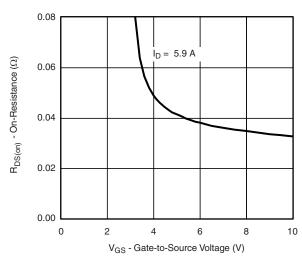


 $V_{\mbox{\footnotesize{DS}}}$ - Drain-to-Source Voltage (V)

Capacitance



On-Resistance vs. Junction Temperature



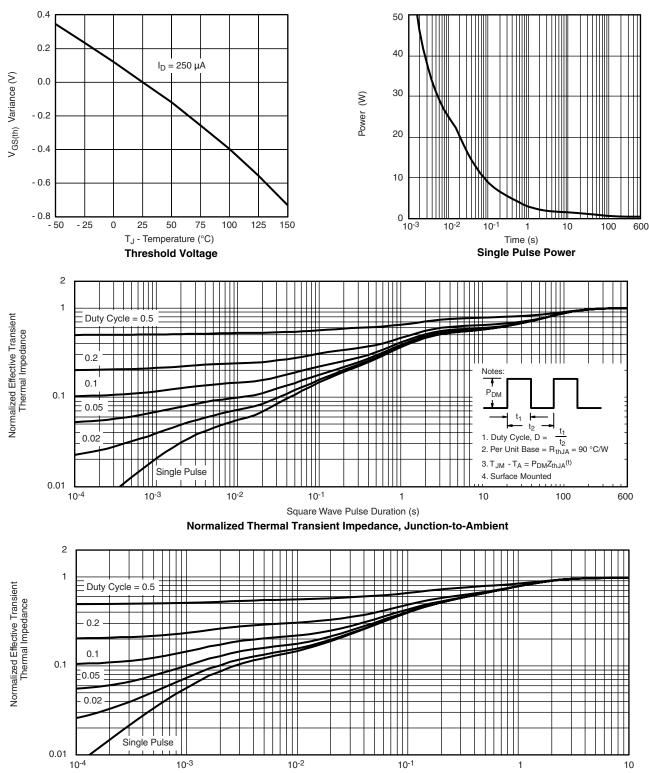
On-Resistance vs. Gate-to-Source Voltage

Is - Source Current (A)

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Square Wave Pulse Duration (s)

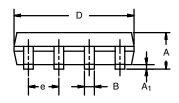
Normalized Thermal Transient Impedance, Junction-to-Foot

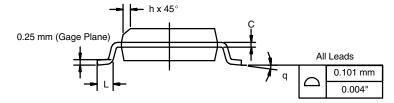
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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INC	HES	
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
Е	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I. 11-Sep-06					

DWG: 5498

Document Number: 71192 www.vishay.com 11-Sep-06

APPLICATION NOTE



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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